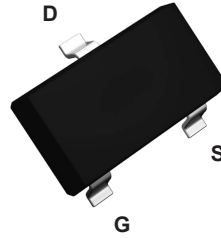
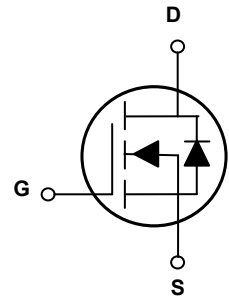


## Main Product Characteristics

$V_{(BR)DSS}$	60V
$R_{DS(ON)}$	90mΩ (max.)
$I_D$	3.0A



SOT-23



Schematic Diagram

## Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



## Description

The SSF6092G1 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

## Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous ( $T_A=25^\circ\text{C}$ )	$I_D$	3.0	A
Drain Current-Continuous ( $T_A=70^\circ\text{C}$ )		2.4	
Drain Current-Pulsed <sup>1</sup>	$I_{DM}$	12	A
Single Pulse Avalanche Energy <sup>2</sup>	$E_{AS}$	8	mJ
Single Pulse Avalanche Current <sup>2</sup>	$I_{AS}$	12.8	A
Power Dissipation ( $T_A=25^\circ\text{C}$ )	$P_D$	1.31	W
Power Dissipation-De-rate above $25^\circ\text{C}$		0.011	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	92	$^\circ\text{C}/\text{W}$
Operating Junction Temperature Range	$T_J$	-55 To +150	$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-55 To +150	$^\circ\text{C}$

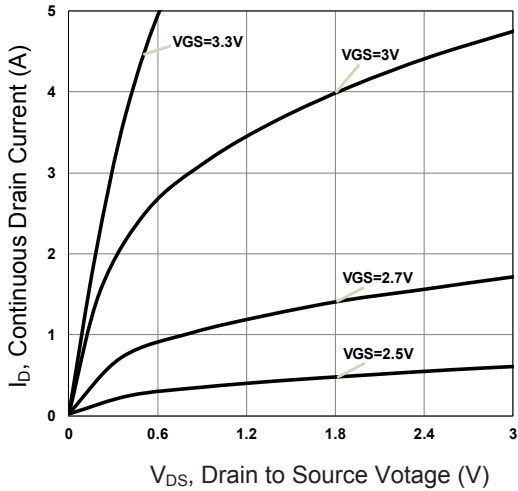
**Electrical Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>On / Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
$BV_{DSS}$ Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to $25^\circ\text{C}$ , $I_D=1mA$	-	0.05	-	$V/^\circ\text{C}$
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS}=60V, V_{GS}=0V,$ $T_J=25^\circ\text{C}$	-	-	1	$\mu A$
		$V_{DS}=48V, V_{GS}=0V,$ $T_J=125^\circ\text{C}$	-	-	10	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=3A$	-	73	90	m $\Omega$
		$V_{GS}=4.5V, I_D=2A$	-	86	118	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.8	2.5	V
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}$		-	-5	-	$mV/^\circ\text{C}$
Forward Transconductance	$g_{fs}$	$V_{DS}=10V, I_D=3A$	-	7	-	S
<b>Dynamic and Switching Characteristics</b>						
Total Gate Charge <sup>2,3</sup>	$Q_g$	$V_{DS}=30V, I_D=3A,$ $V_{GS}=10V$	-	4.6	8	nC
Gate-Source Charge <sup>2,3</sup>	$Q_{gs}$		-	0.4	3	
Gate-Drain Charge <sup>2,3</sup>	$Q_{gd}$		-	2	4	
Turn-On Delay Time <sup>2,3</sup>	$t_{d(on)}$	$V_{DD}=30V, R_G=6\Omega,$ $V_{GS}=10V, I_D=3A$	-	2.9	6	nS
Rise Time <sup>2,3</sup>	$t_r$		-	9.5	18	
Turn-Off Delay Time <sup>2,3</sup>	$t_{d(off)}$		-	18.4	35	
Fall Time <sup>2,3</sup>	$t_f$		-	5.3	10	
Input Capacitance	$C_{iss}$	$V_{DS}=30V, V_{GS}=0V,$ $F=1MHz$	-	360	540	pF
Output Capacitance	$C_{oss}$		-	30	45	
Reverse Transfer Capacitance	$C_{rss}$		-	20	30	
Gate Resistance	$R_g$	$V_{GS}=0V, V_{DS}=0V,$ $F=1MHz$	-	2	4	$\Omega$
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Continuous Source Current	$I_S$	$V_G=V_D=0V,$ Force Current	-	-	5	A
Pulsed Source Current	$I_{SM}$		-	-	20	A
Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=1A,$ $T_J=25^\circ\text{C}$	-	-	1	V
Reverse Recovery Time <sup>2</sup>	$t_{rr}$	$V_R=50V, I_S=3A,$ $di/dt=100A/\mu s,$ $T_J=25^\circ\text{C}$	-	25	-	nS
Reverse Recovery Charge <sup>2</sup>	$Q_{rr}$		-	15	-	nC

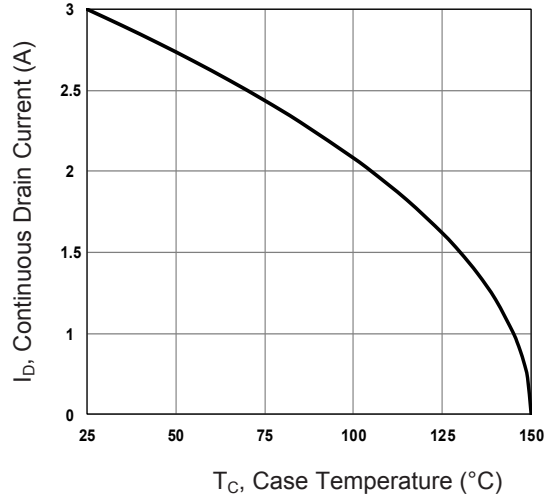
Note:

1. Repetitive rating: Pulsed width limited by maximum junction temperature.
2.  $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=12.8A, R_G=25\Omega,$  starting  $T_J=25^\circ\text{C}$ .
3. Pulse test: pulse width  $\leq 300\mu s,$  duty cycle  $\leq 2\%$ .

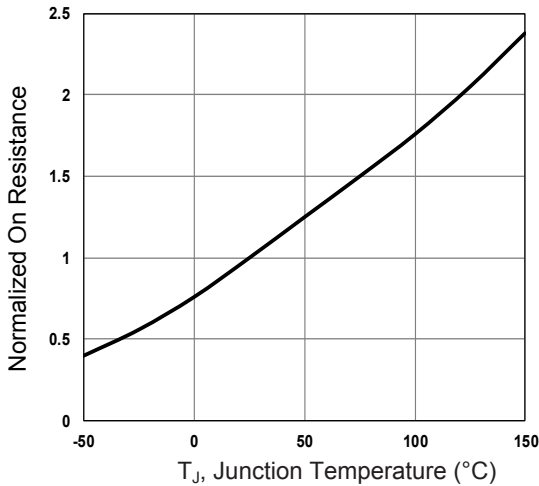
**Typical Electrical and Thermal Characteristic Curves**



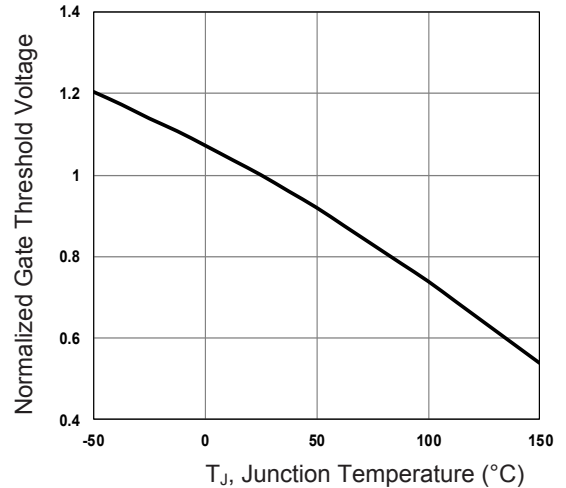
**Figure 1. Typical Output Characteristics**



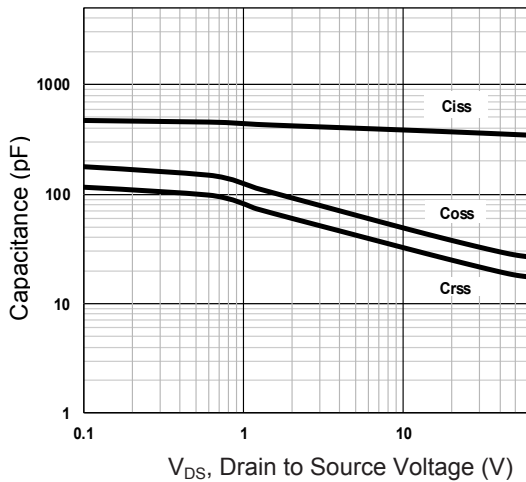
**Figure 2. Continuous Drain Current vs.  $T_C$**



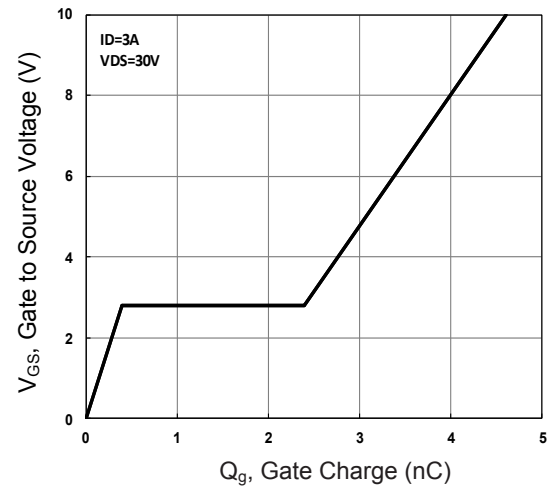
**Figure 3. Normalized  $R_{DS(ON)}$  vs.  $T_J$**



**Figure 4. Normalized  $V_{th}$  vs.  $T_J$**

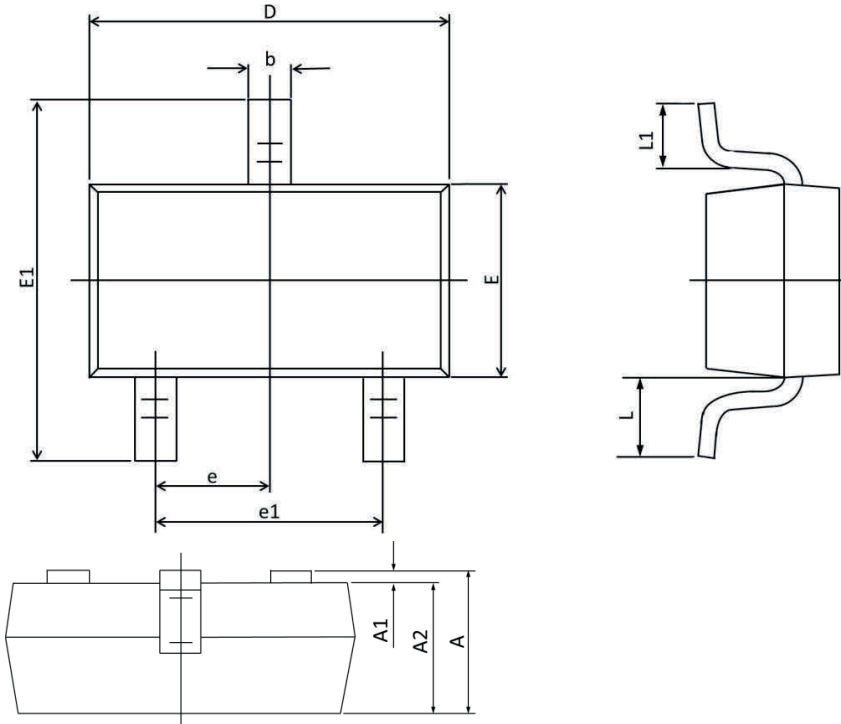


**Figure 5. Capacitance Characteristics**



**Figure 6. Gate Charge Characteristics**

**Package Outline Dimensions (SOT-23)**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.200	0.035	0.047
A1	0.000	0.100	0.000	0.004
A2	0.900	1.150	0.035	0.045
b	0.300	0.500	0.012	0.020
D	2.800	3.040	0.110	0.120
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.95 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.55 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020

**Order Information**

Device	Package	Marking	Carrier	Quantity
SSF6092G1	SOT-23	6092	Tape & Reel	3,000pcs / Reel

For more information, please contact us at: [inquiry@goodarksemi.com](mailto:inquiry@goodarksemi.com)